

## TURBO 2 ULTRAFAST HIGH VOLTAGE RECTIFIER

**Table 1: Main Product Characteristics**

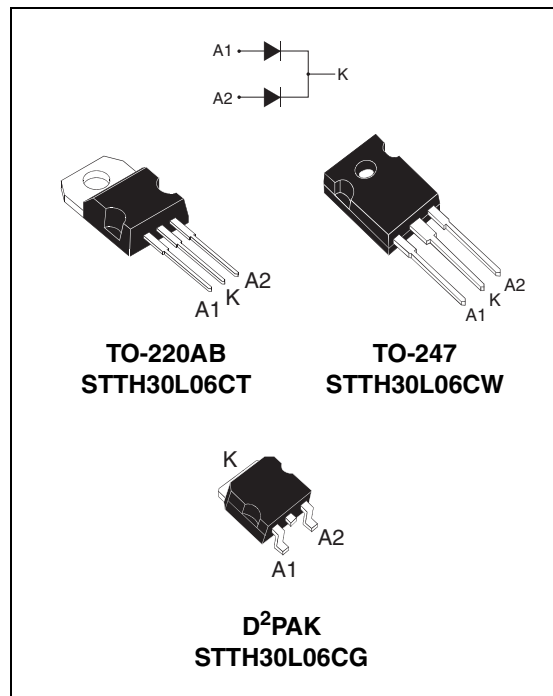
$I_{F(AV)}$	Up to 2 x 20 A
$V_{RRM}$	600 V
$T_j$	175°C
$V_F$ (typ)	0.95 V
$t_{rr}$ (max)	55 ns

### FEATURES AND BENEFITS

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching & conduction losses

### DESCRIPTION

The STTH30L06, which is using ST Turbo 2 600V technology, is specially suited for use in switching power supplies, and industrial applications, as rectification and discontinuous mode PFC boost diode.



**Table 2: Order Codes**

Part Number	Marking
STTH30L06CT	STTH30L06CT
STTH30L06CW	STTH30L06CW

Part Number	Marking
STTH30L06CG	STTH30L06CG
STTH30L06GG-TR	STTH30L06CG

**Table 3: Absolute Ratings** (limiting values, per diode)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage	600	V	
$I_{F(RMS)}$	RMS forward current	30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 140^\circ\text{C}$ Per diode	15	A
		$T_c = 125^\circ\text{C}$ Per device	30	
		$T_c = 120^\circ\text{C}$ Per diode	20	
		$T_c = 110^\circ\text{C}$ Per device	40	
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ms}$ sinusoidal	130	A
$T_{stg}$	Storage temperature range	-65 to + 175	°C	
$T_j$	Maximum operating junction temperature	175	°C	

**Table 4: Thermal Resistance**

Symbol	Parameter		Value (max).	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	1.7	°C/W
		Total	1.15	
R <sub>th(c)</sub>	Coupling		0.6	°C/W

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

**Table 5: Static Electrical Characteristics (per diode)**

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			15	µA
		T <sub>j</sub> = 150°C			40	400	
V <sub>F</sub> **	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15A			1.55	V
		T <sub>j</sub> = 150°C			0.95	1.2	
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 30A			1.76	
		T <sub>j</sub> = 150°C			1.15	1.45	

Pulse test: \* tp = 5 ms, δ < 2%

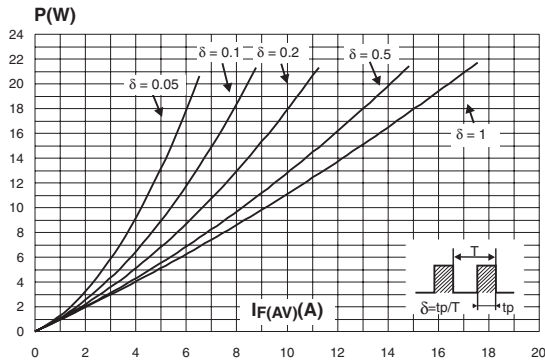
\*\* tp = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:  $P = 0.94 \times I_F(\text{AV}) + 0.017 I_F^2(\text{RMS})$

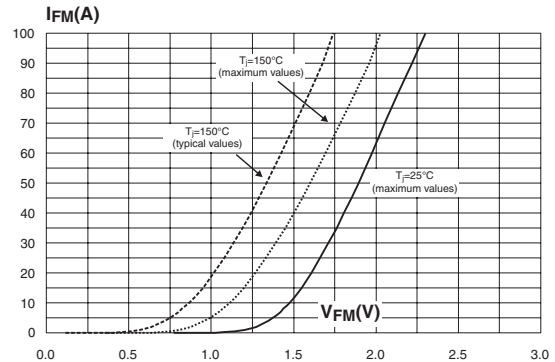
**Table 6: Dynamic Characteristics (per diode)**

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	T <sub>j</sub> = 25°C	I <sub>F</sub> = 0.5A I <sub>rr</sub> = 0.25A I <sub>R</sub> = 1A			55	ns
			I <sub>F</sub> = 1A dI <sub>F</sub> /dt = 50 A/µs V <sub>R</sub> = 30V		60	85	
I <sub>RM</sub>	Reverse recovery current	T <sub>j</sub> = 125°C	I <sub>F</sub> = 15A V <sub>R</sub> = 400V dI <sub>F</sub> /dt = 100 A/µs		8.5	12	A
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15A dI <sub>F</sub> /dt = 100 A/µs V <sub>FR</sub> = 1.1 x V <sub>Fmax</sub>			300	ns
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15A dI <sub>F</sub> /dt = 100 A/µs V <sub>FR</sub> = 1.1 x V <sub>Fmax</sub>		3.0		V

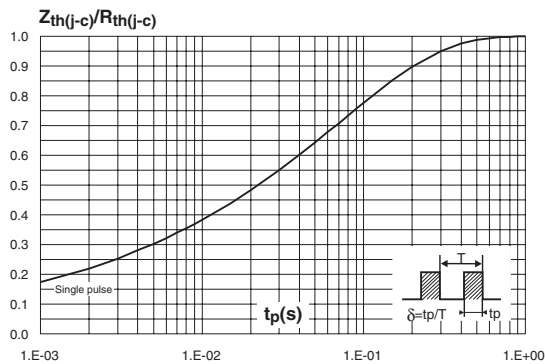
**Figure 1: Conduction losses versus average forward current (per diode)**



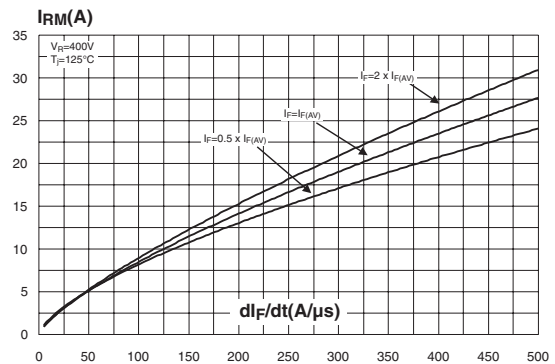
**Figure 2: Forward voltage drop versus forward current (per diode)**



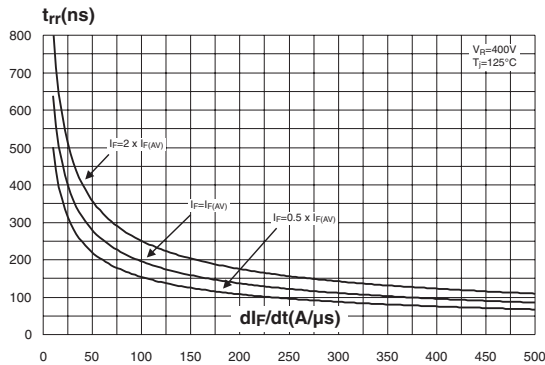
**Figure 3: Relative variation of thermal impedance junction to case versus pulse duration**



**Figure 4: Peak reverse recovery current versus dIF/dt (typical values, per diode)**



**Figure 5: Reverse recovery time versus dIF/dt (typical values, per diode)**



**Figure 6: Reverse recovery charges versus dIF/dt (typical values, per diode)**

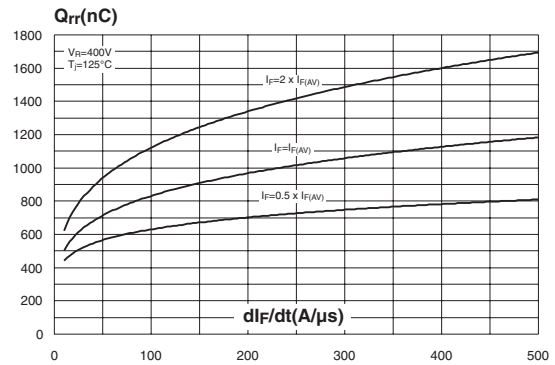


Figure 7: Reverse recovery softness factor versus  $di_F/dt$  (typical values, per diode)

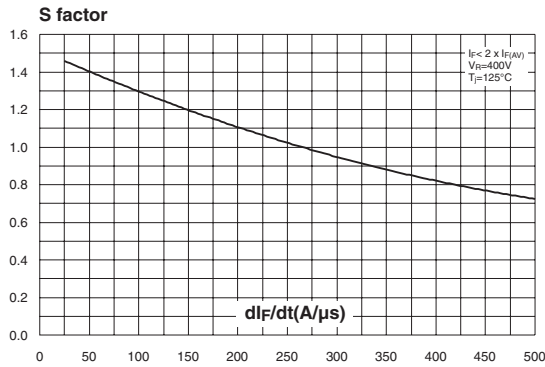


Figure 8: Relative variations of dynamic parameters versus junction temperature

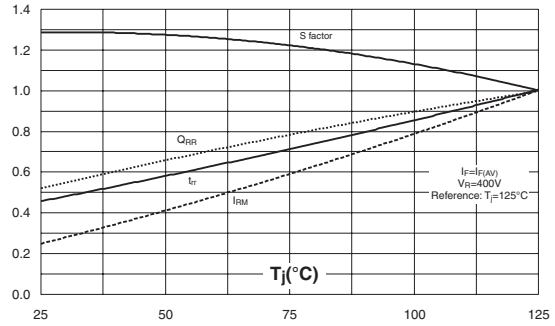


Figure 9: Transient peak forward voltage versus  $di_F/dt$  (typical values, per diode)

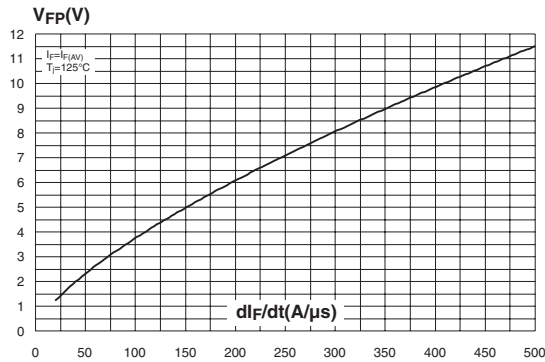


Figure 10: Forward recovery time versus  $di_F/dt$  (typical values, per diode)

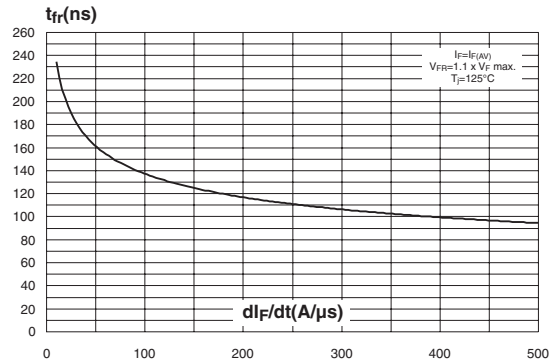


Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)

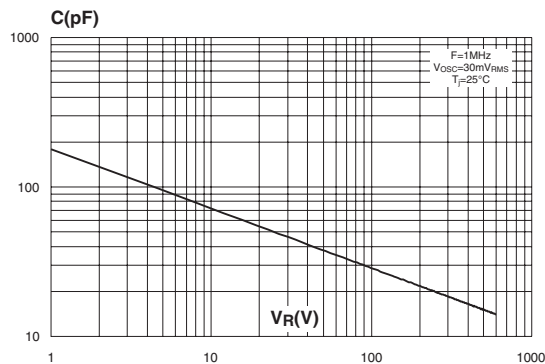


Figure 12: Thermal resistance junction to ambient versus copper surface under tab (epoxy FR4,  $e_{Cu}=35\mu m$ ) (D<sup>2</sup>PAK)

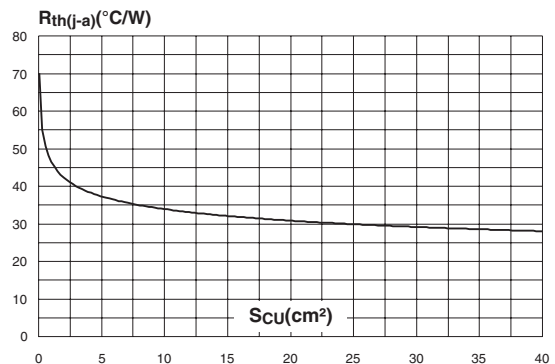


Figure 13: TO-247 Package Mechanical Data

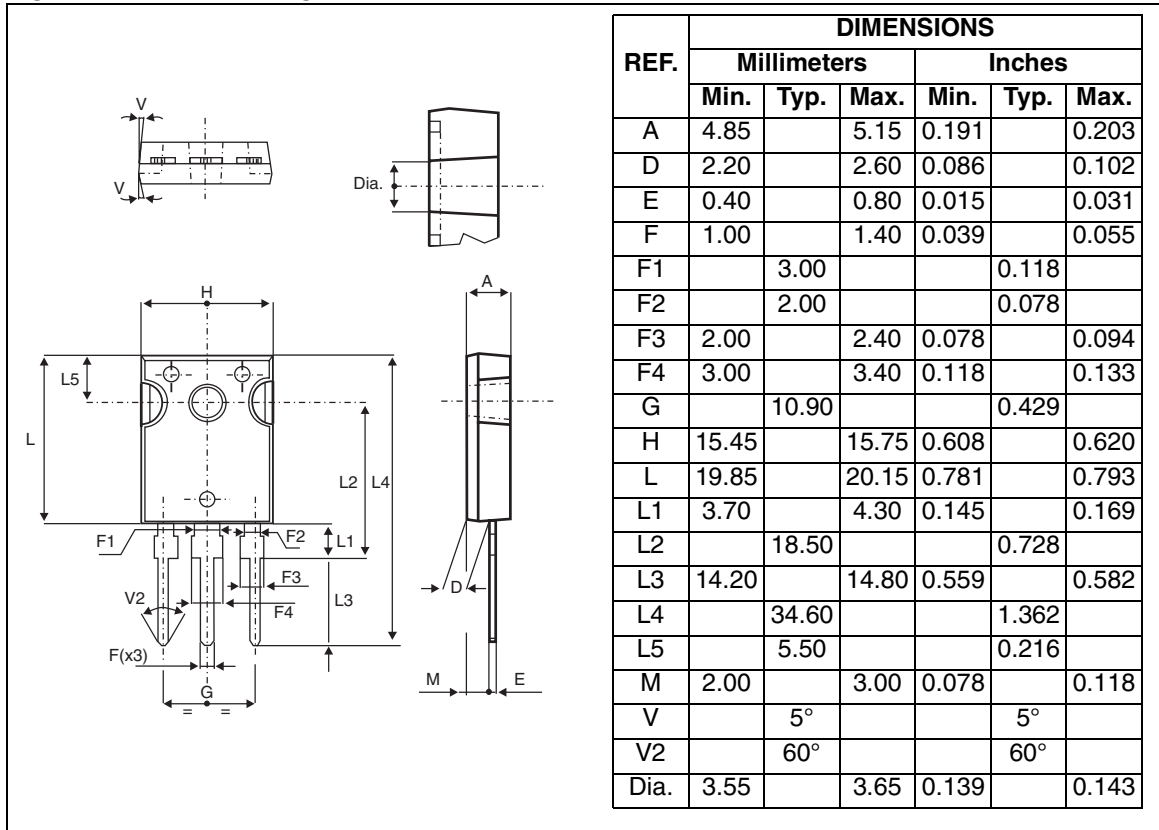


Figure 14: D<sup>2</sup>PAK Package Mechanical Data

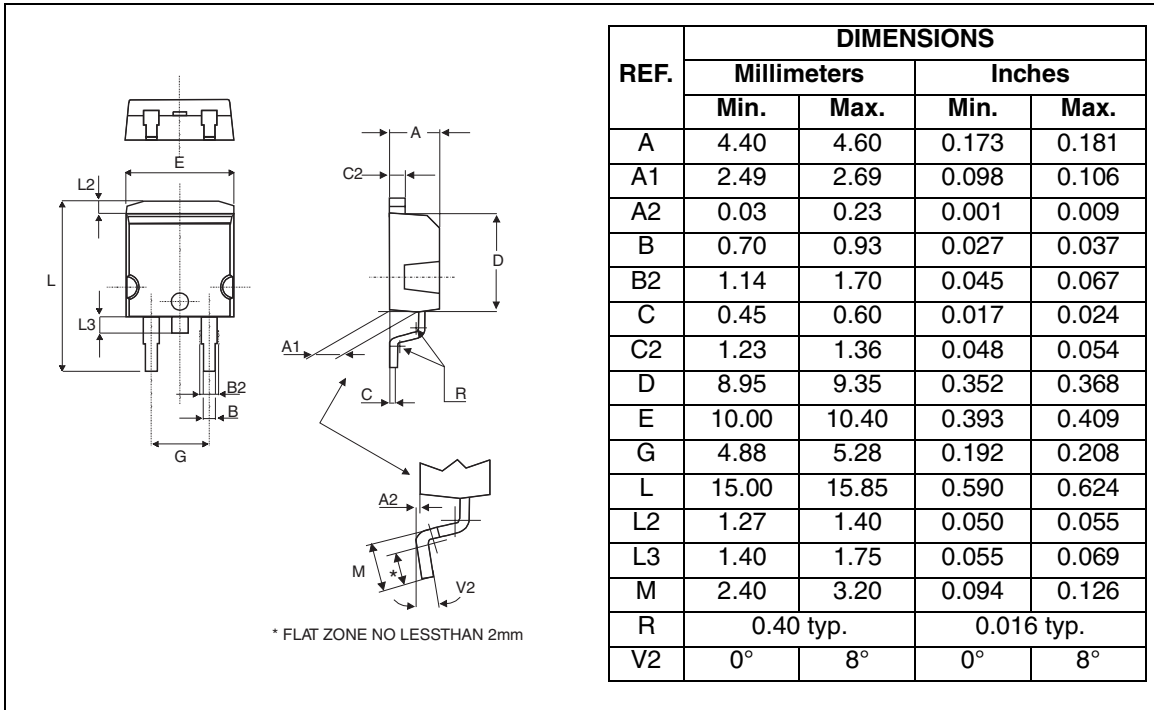


Figure 15: D<sup>2</sup>PAK Foot Print Dimensions (in millimeters)

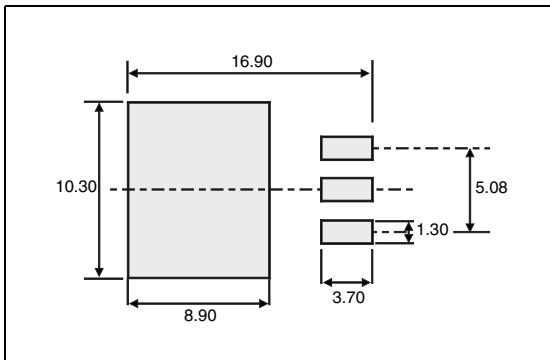


Figure 16: TO-220AB Package Mechanical Data

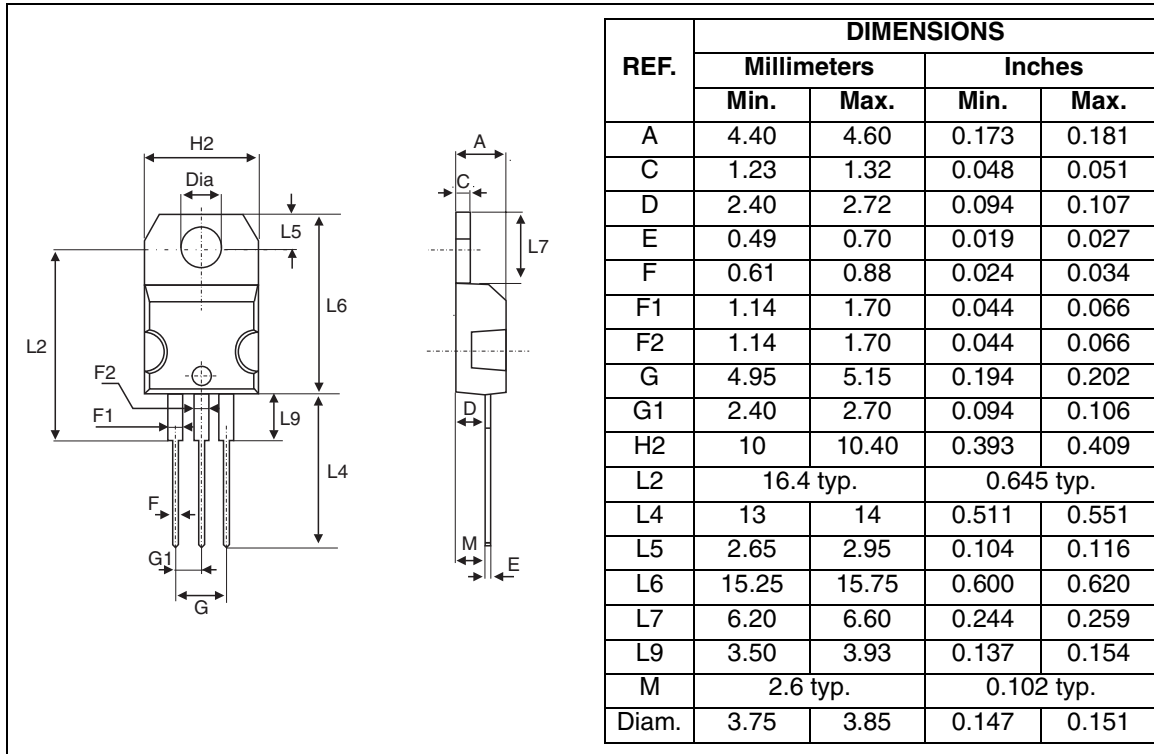


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH30L06CT	STTH30L06CT	TO-220AB	2.23 g	50	Tube
STTH30L06CG	STTH30L06CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STTH30L06CG-TR	STTH30L06CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & eel
STTH30L06CW	STTH30L06CW	TO-247	4.46 g	50	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 m.N. (TO-220FPAC) / 0.55 m.N. (TO-220AB)
- Maximum torque value: 1.0 m.N. (TO-220FPAC) / 0.70 m.N. (TO-220AB)

Table 8: Revision History

Date	Revision	Description of Changes
07-Sep-2004	1	First issue

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